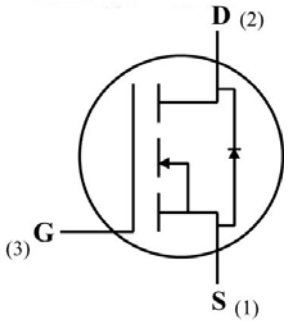
Silicon Carbide Power MOSFET （N-Channel Enhancement）

V_{DS}	1200V
$I_{D\ (25°C)}$	21A
$R_{DS(on)}$	160mΩ



Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant
- AEC-Q101 qualified

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package**: TO-247AB
- **Terminals**: Tin plated leads
- **Polarity**: As marked

■Maximum Ratings (T_C=25℃ Unless otherwise specified）

PARAMTETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code			D2120160NCTG1Q		
Drain source voltage @ T_j=25°C	$V_{DS,max}$	V	1200	V_{GS}=0 V, I_D=100uA	
Gate source voltage @ T_j=25°C	$V_{GS,max}$	V	-10/+25	Absolute maximum values	
Gate source voltage @ T_j=25°C	$V_{GS,op}$	V	-5/+20	Recommended operational values	Note1、2
Continuous drain current @ T_c=25°C	I_D	A	21	V_{GS}=20V, Tc=25℃	Fig.18
Continuous drain current @ T_c=100°C			15	V_{GS}=20V, Tc=100℃	
Pulsed drain current	$I_{D(pulsed)}$	A	40	Pulse width t_p limited by $T_{j,max}$	Fig.23
Power Dissipation	P_{TOT}	W	157	T_c=25°C , Tj = 175℃	Fig.17
Power Dissipation			68	T_c=110°C, Tj = 175℃	
Operating junction and Storage temperature range	Tj ,Tstg	°C	-55 to +175		
Soldering temperature	T_L	°C	260	1.6mm (0.063'') from case for 10s	
Mounting torque	T_M	Nm	0.6	M3 screw Maximum of mounting process: 3	

■Static Electrical Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	2.0	3.0	4.0	V_{DS}=V_{GS}, I_D= 2.5mA	Fig.4, 11
				2.4		V_{DS}=V_{GS}, I_D= 2.5mA, Tj=175℃	
Drain source breakdown voltage	$V_{(BR)DSS}$	V	1200			V_{GS}=0, I_D=100uA	
Zero gate voltage drain current	I_{DSS}	uA		1	10	V_{DS}=1200V, V_{GS}= 0V	Fig.16
Gate source leakage current	I_{GSS}	nA			100	V_{GS}= 20V, V_{DS}=0V	
Current drain source on-state resistance	$R_{DS\ ON}$	mΩ		155	160	V_{GS}=20V, I_D=10A	Fig.5, 6, 7
				320		V_{GS}=20V, I_D=10A,Tj=175℃	
Internal gate resistance	Rg	Ω		6.5		f=1MHz, V_{AC}=25mV	
Diode forward voltage	V_{SD}	V		4.3		V_{GS}=-5V, I_{SD}=5A	Fig.8
				3.1		V_{GS}=0V, I_{SD}=5A,Tj=175℃	Fig.9
Transconductance	g_f	S		4.0		V_{DS}=15V,I_D=10A	Fig.4
				5.3		V_{DS}=15V,I_D=10A,Tj=175℃	

■Dynamic Electrical Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	Ciss	pF		675		V_{DS}=1000V, V_{GS}=0V, Tj=25℃, f=100kHz, V_{AC} = 25mV	Fig.13, 14
Output capacitance	Coss			47			
Reverse capacitance	Crss			3.8			
Coss stored energy	Eoss	uJ		20			Fig.15
Gate source charge	Qgs	nC		9		V_{DS}=800V, V_{GS}=-5/20V, I_D=10A	Fig.12
Gate drain charge	Qgd			19			
Gate charge	Qg			39			

■Switching Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on switching energy	E_{on}	uJ		115		V_{DD}=800V, V_{GS}=-5/+20V, I_D=10A, Rg=2.5Ω, L=434uH	Fig.21, 22
Turn off switching energy	E_{off}			52			
Turn on delay time	$t_{d(on)}$	ns		7			
Rise time	t_r			9			
Turn off delay time	$t_{d(off)}$	ns		13		V_{DD}=800V, V_{GS}=-5/+20V, I_D=10A, Rg=2.5Ω, L=434uH	Fig.21, 22
Fall time	t_f			14			

■Body diode characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V_{SD}	V		4.3		V_{GS}=-5V, I_{SD}=5A	Fig.8
				3.1		V_{GS}=0V, I_{SD}=5A,Tj=175℃	Fig.9
Continuous diode forward current	I_S	A		24		Tc=25℃	Note1
Reverse recovery time	trr	nS		22		V_R=800V, V_{GS}=-5V, I_D=10A, di/dt=2400A/uS	
Reverse recovery charge	Qrr	nC		195			
Peak reverse recovery current	Irrm	A		17			

Note 1: When using SiC Body Diode the maximun recommended V_{GS} = -5V
Note 2: MOSFET can also safely operate at 0/20 V

■Thermal Characteristics （T_a=25℃ Unless otherwise specified）

PARAMETER	SYMBOL	UNIT	Typ.	Max.
Thermal resistance	$R_{\theta J-C}$	°C /W	0.9	0.95

■Typical Characteristics

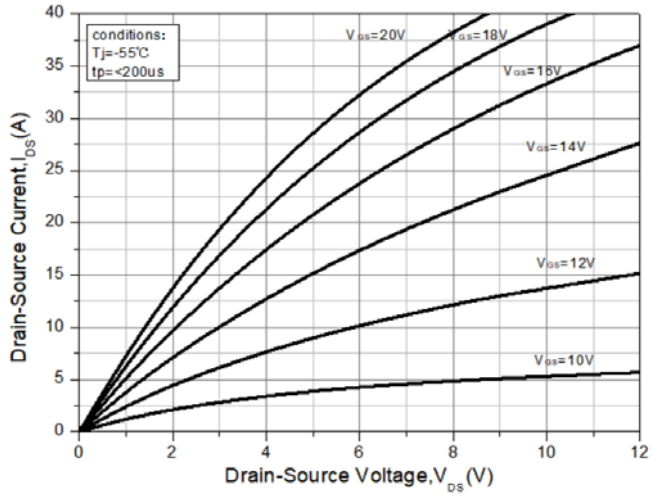


Figure 1. Output Characteristics Tj = -55℃

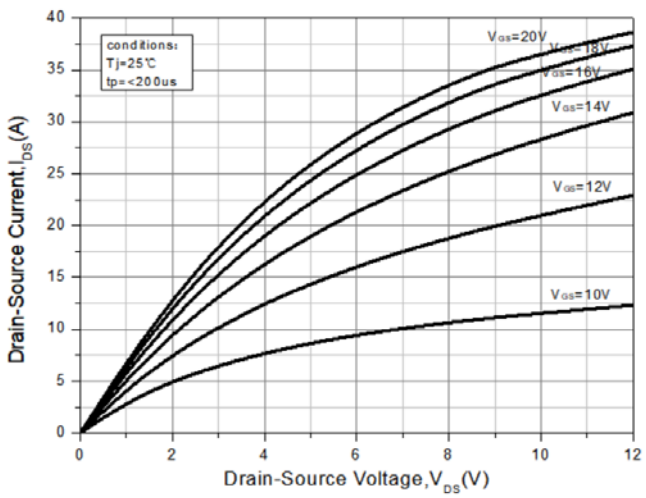


Figure2. Output Characteristics Tj = 25℃

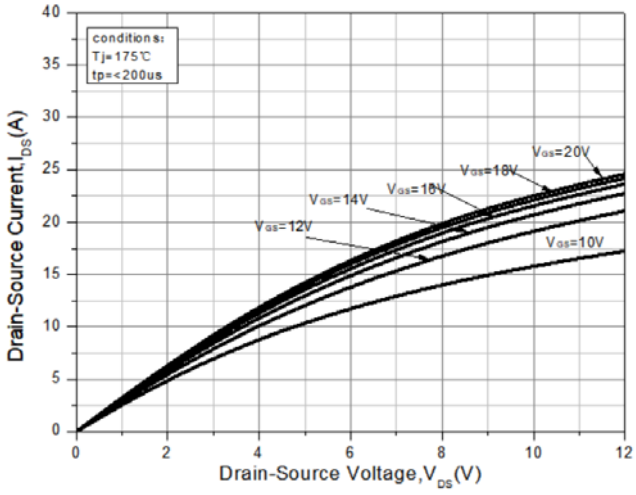


Figure 3. Output Characteristics Tj = 175℃

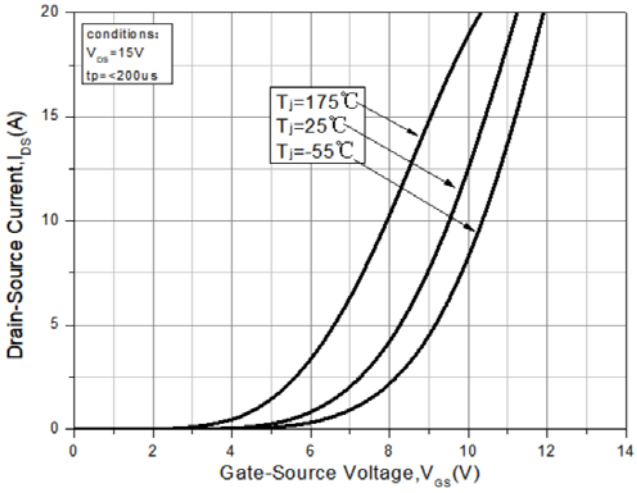


Figure 4. Transfer Characteristics for various junction temperature

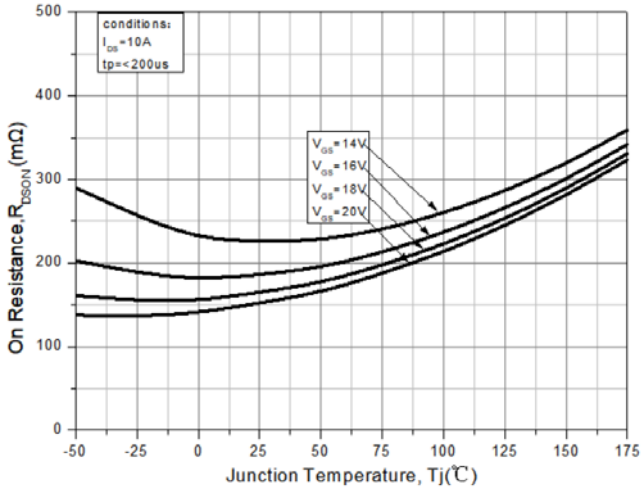


Figure 5. On-resistance vs.temperature for various gate voltage

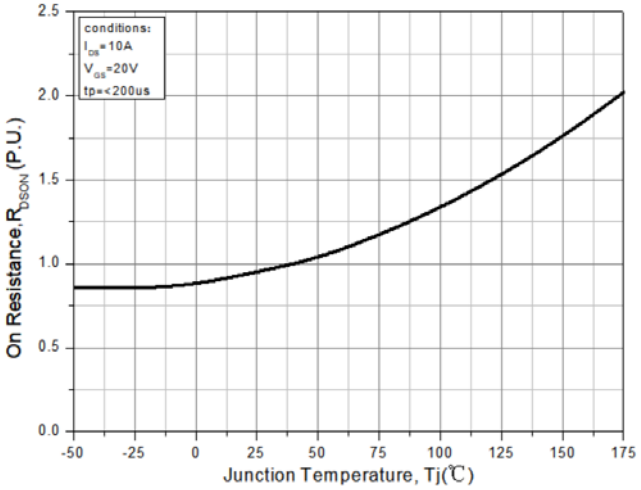


Figure 6. Normalized on-resistance vs.temperature

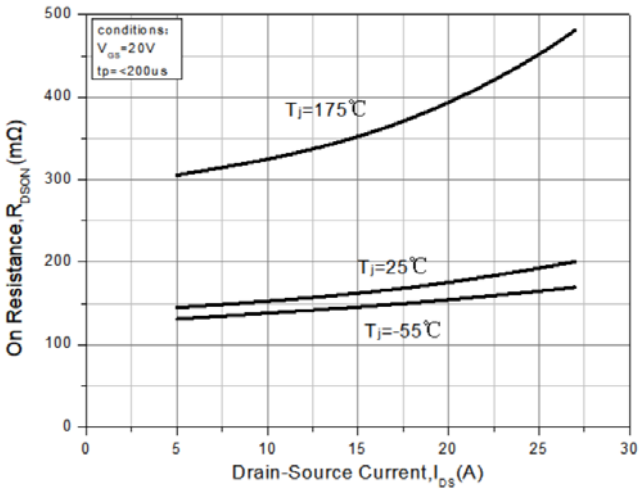


Figure 7. On-resistance vs. drain current

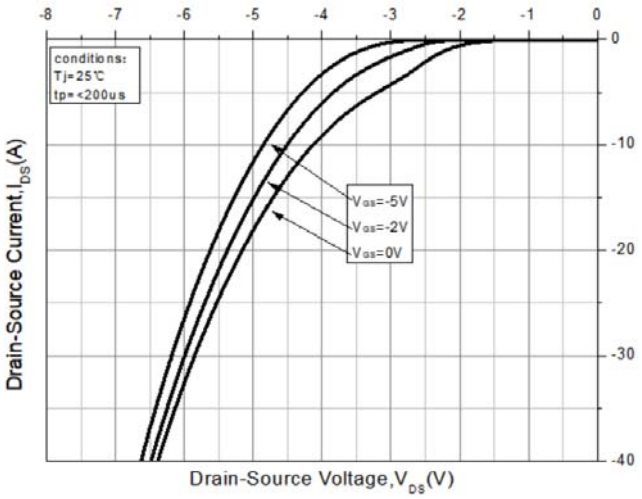


Figure 8. Body diode characteristic at Tj= 25 ℃

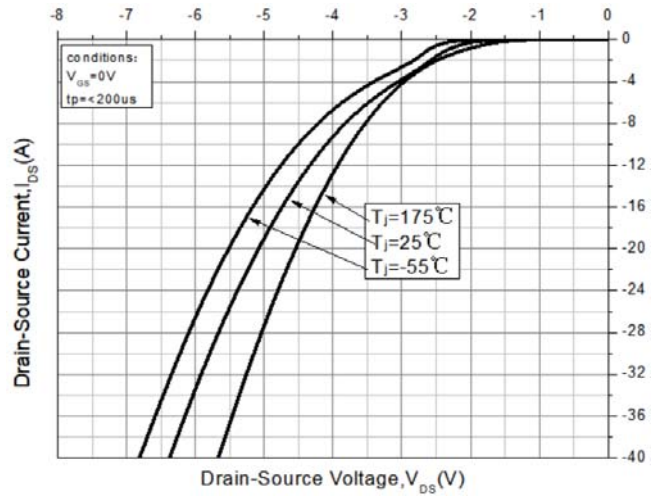


Figure 9. Body diode characteristic

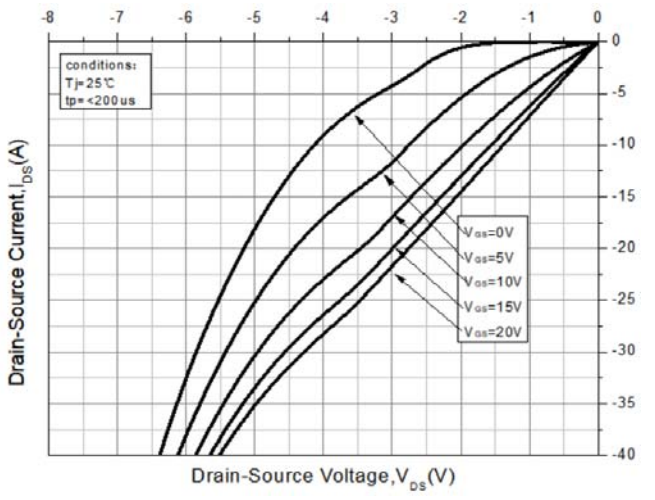


Figure 10. 3rd quadrant characteristic at Tj= 25 ℃

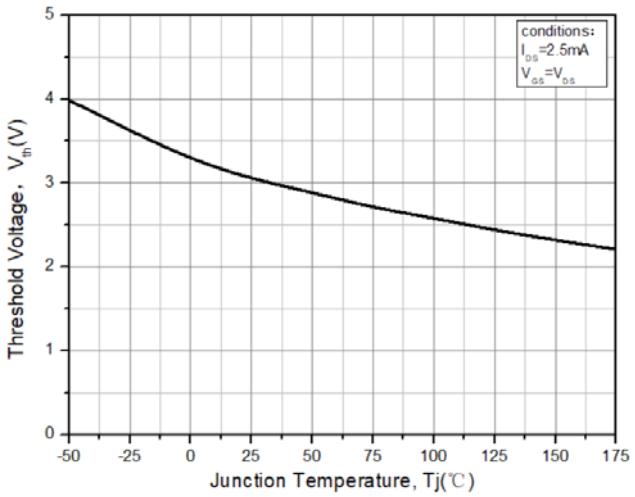


Figure 11. Threshold voltage vs.temperature

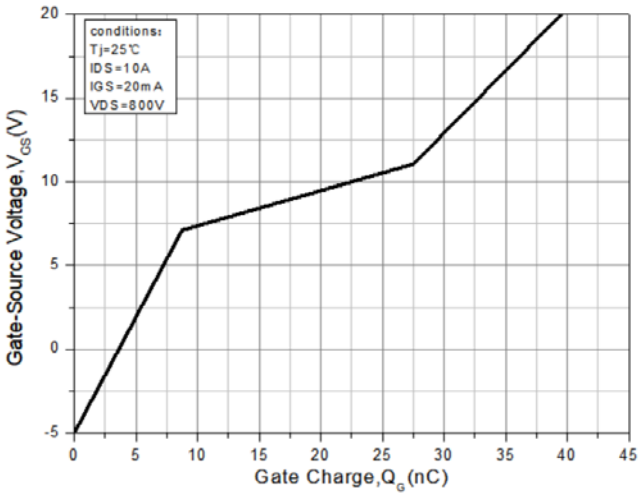


Figure 12. Gate charge characteristic

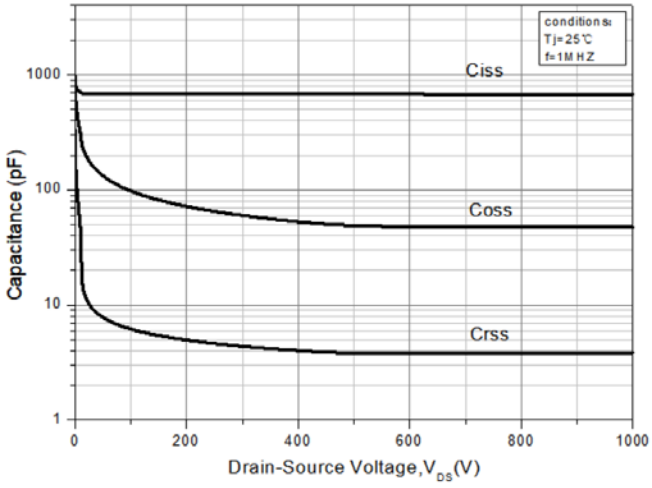


Figure 13. Capacitances vs.drain source voltage (0-1000V)

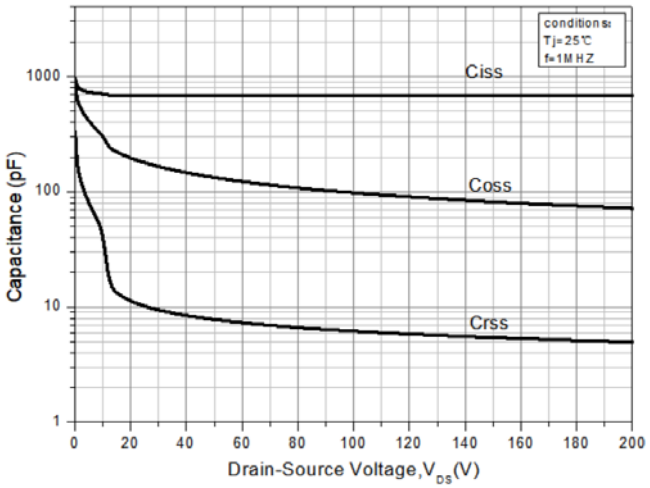


Figure 14. Capacitances vs.drain source voltage (0-200V)

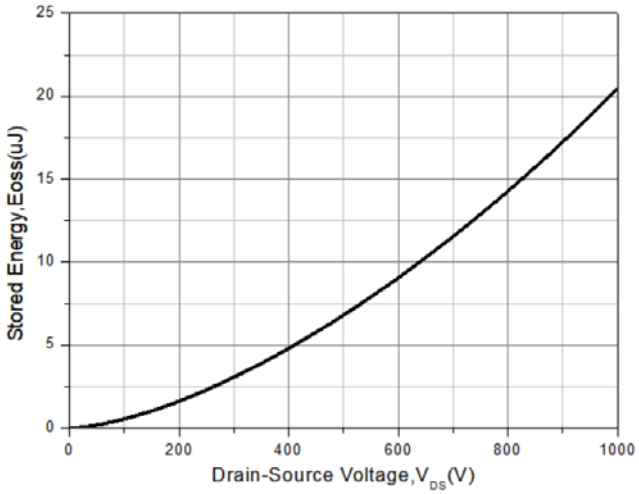


Figure 15. Output capacitor stored energy

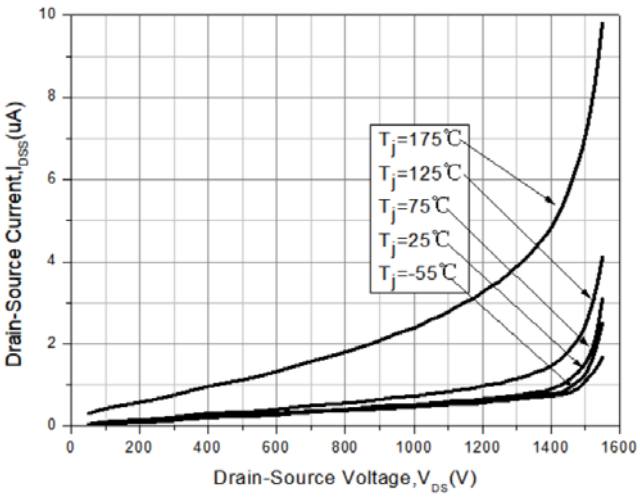


Figure 16. Reverse characteristics vs. Tj

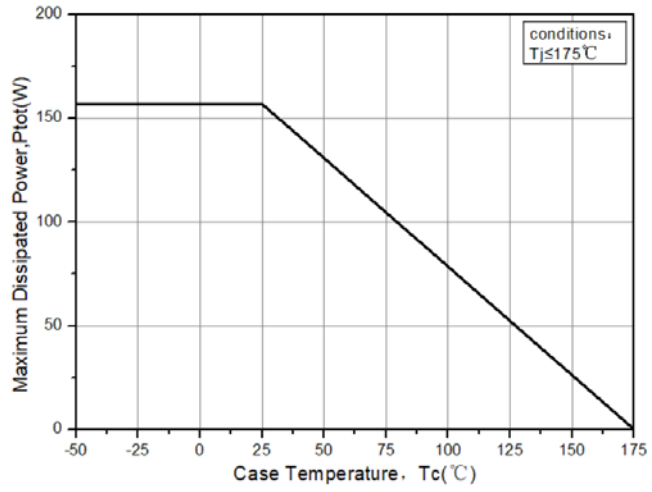


Figure 17. Maximun power dissipation derating vs. case temperatere

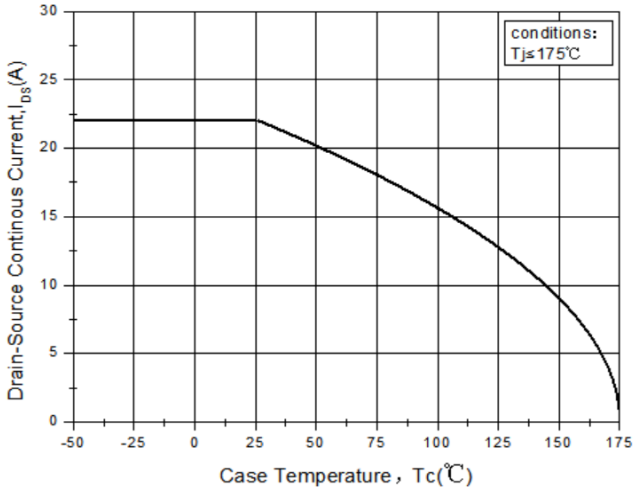


Figure 18. Coutinuous drain current derating vs. case temperatere

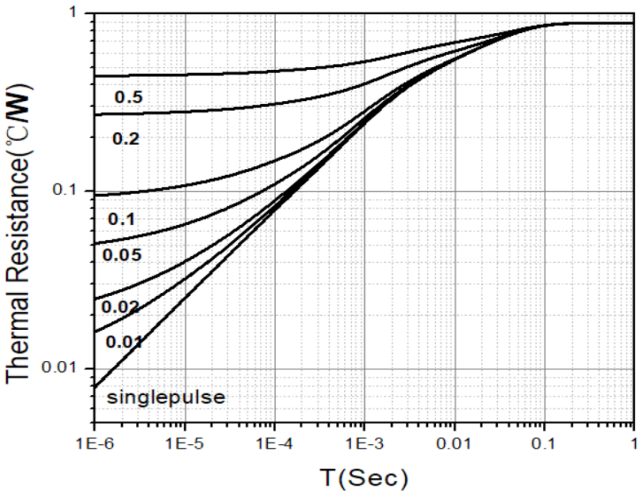


Figure 19. Transient thermal impedance (junction - case)

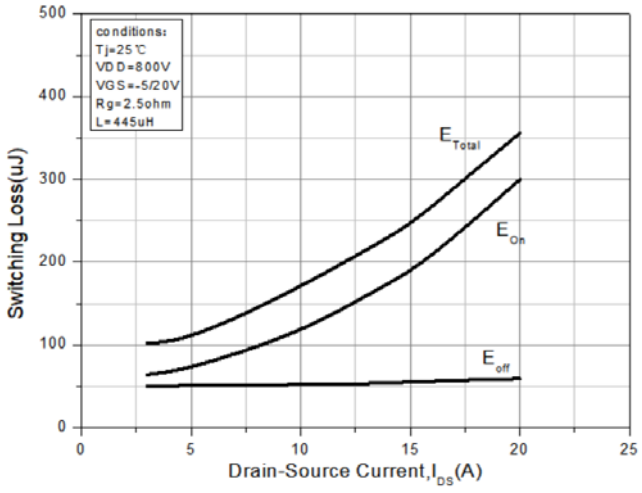


Figure 20. Clamped Inductive switching energy vs. darin current

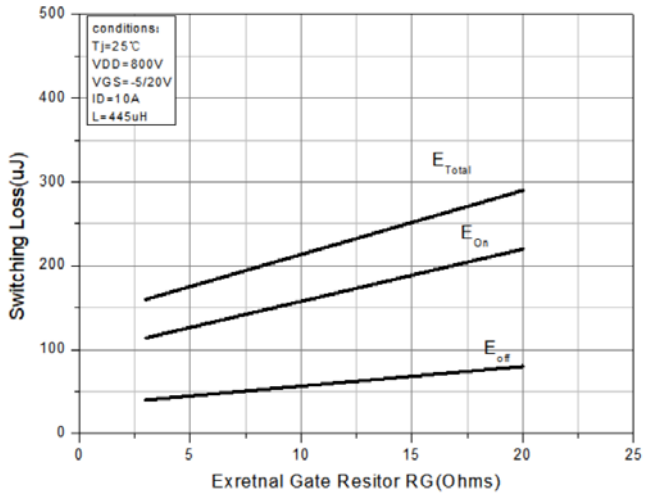


Figure 21. Clamped inductive switching energy vs. Rg

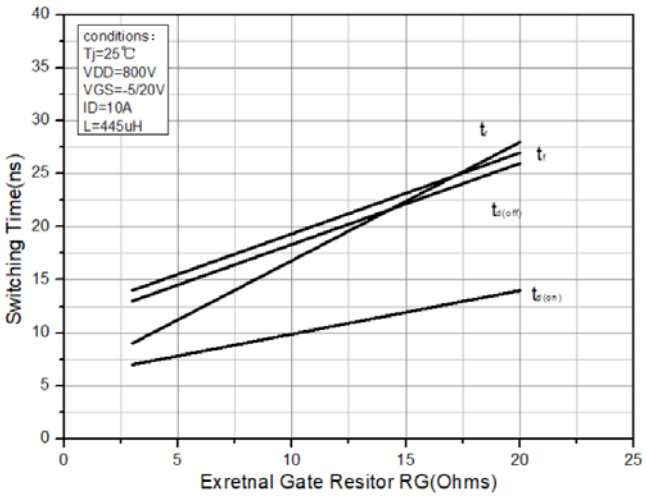


Figure 22. Switching times vs. Rg

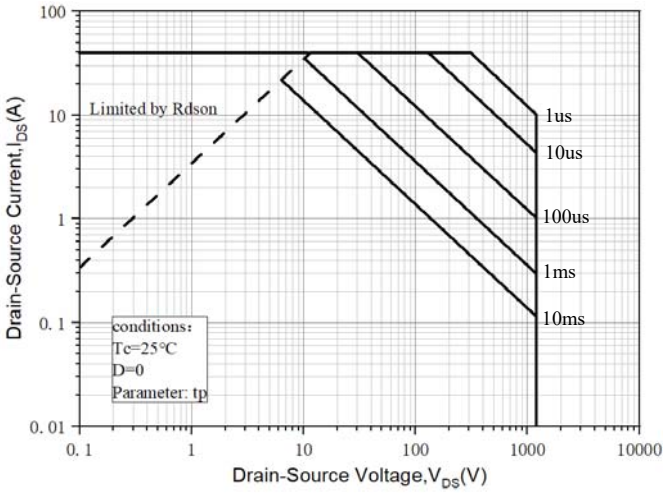


Figure 23. Safe Operating Area

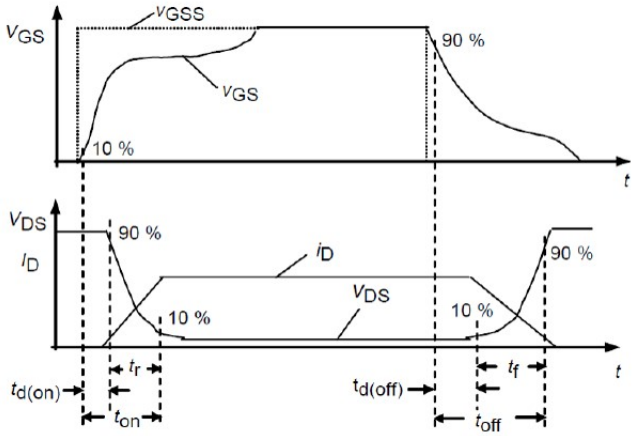


Figure 24. Switching Times Definition

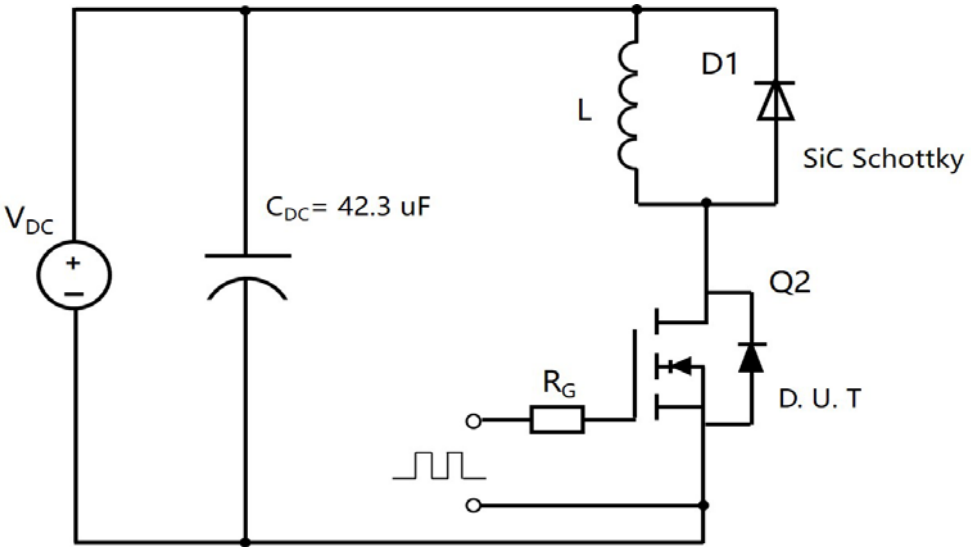
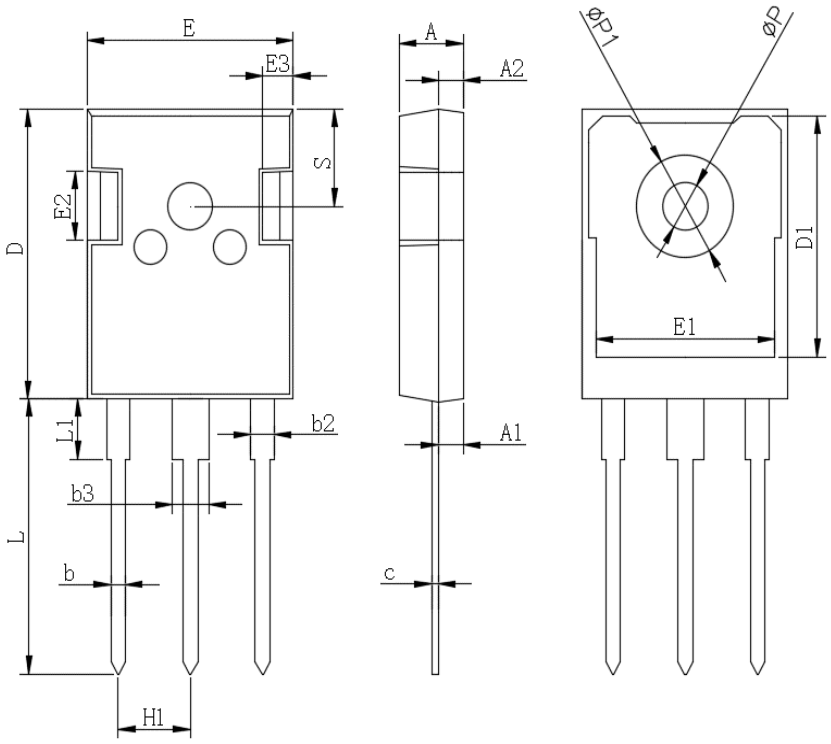


Figure 25. Clamped Inductive Switching Waveform Test Circuit

■Outline Dimensions

TO-247AB



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
ΦP	3.40	3.80
ΦP1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20

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